

**What is claimed is:**

**1. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated.**

**2. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with an oxidizing agent.**

**3. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with blowing of ozone to the ground or polished surface thereof.**

**4. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with ozone water.**

**5. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is**

implemented with illumination of the ground or polished surface thereof with ultraviolet.

5 6. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

10 7. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with an oxidizing agent, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the  
15 deactivation treatment.

8. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is  
20 implemented with blowing of ozone to the ground or polished surface thereof, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

9. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a  
25 grinding or polishing step, with semiconductor circuits formed

thereon, is deactivated, wherein the deactivation treatment is implemented with ozone water, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

5           10. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with illumination of the ground or polished surface  
10 thereof with ultraviolet, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

11. A dicing sheet adhering apparatus having a mechanism to blow ozone to a ground or polished surface of a wafer.

15           12. A dicing sheet adhering apparatus having a UV illumination mechanism illuminating a UV-setting protective tape on a ground or polished surface of a wafer with ultraviolet and in addition, a mechanism to blow exhaust having cooled a UV lamp to the ground or polished surface of a wafer.

20